

MMBT6517LT1

High Voltage Transistor

NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	350	V
Collector - Base Voltage	V_{CBO}	350	V
Emitter - Base Voltage	V_{EBO}	5.0	V
Base Current	I_B	25	mA
Collector Current - Continuous	I_C	100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

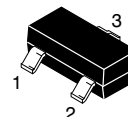
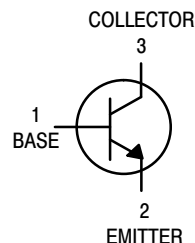
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



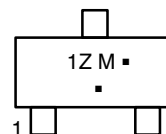
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SOT-23 (TO-236AB)
CASE 318
STYLE 6

MARKING DIAGRAM



1Z = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$)	$V_{(BR)CEO}$	350	–	V
Collector – Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	350	–	V
Emitter – Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	6.0	–	V
Collector Cutoff Current ($V_{CB} = 250\text{ V}$)	I_{CBO}	–	50	nA
Emitter Cutoff Current ($V_{EB} = 5.0\text{ V}$)	I_{EBO}	–	50	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ V}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ V}$) ($I_C = 30\text{ mA}$, $V_{CE} = 10\text{ V}$) ($I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$) ($I_C = 100\text{ mA}$, $V_{CE} = 10\text{ V}$)	h_{FE}	20 30 30 20 15	– – 200 200 –	–
Collector – Emitter Saturation Voltage (Note 3) ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$) ($I_C = 30\text{ mA}$, $I_B = 3.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	– – – –	0.30 0.35 0.50 1.0	V
Base – Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$) ($I_C = 30\text{ mA}$, $I_B = 3.0\text{ mA}$)	$V_{BE(sat)}$	– – –	0.75 0.85 0.90	V
Base – Emitter On Voltage ($I_C = 100\text{ mA}$, $V_{CE} = 10\text{ V}$)	$V_{BE(on)}$	–	2.0	V

SMALL-SIGNAL CHARACTERISTICS

Current Gain – Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ V}$, $f = 20\text{ MHz}$)	f_T	40	200	MHz
Collector–Base Capacitance ($V_{CB} = 20\text{ V}$, $f = 1.0\text{ MHz}$)	C_{cb}	–	6.0	pF
Emitter–Base Capacitance ($V_{EB} = 0.5\text{ V}$, $f = 1.0\text{ MHz}$)	C_{eb}	–	80	pF

3. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

ORDERING INFORMATION

Device Order Number	Package Type	Tape and Reel Size [†]
MMBT6517LT1	SOT-23	3,000 / Tape & Reel
MMBT6517LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT6517LT3	SOT-23	10,000 / Tape & Reel
MMBT6517LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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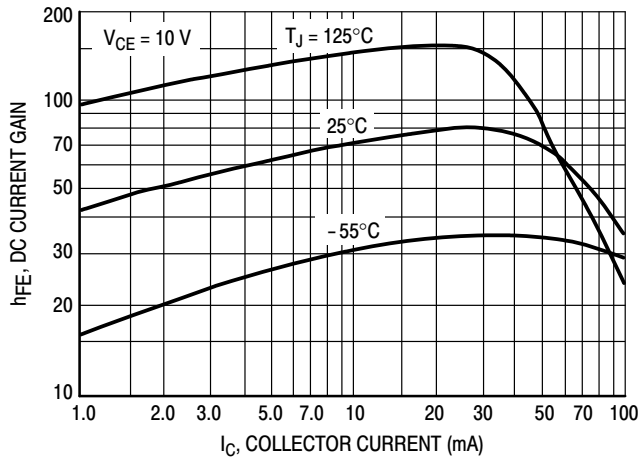


Figure 1. DC Current Gain

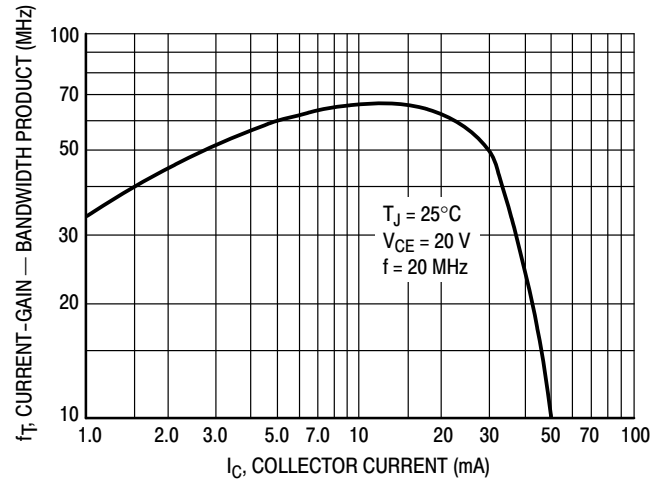


Figure 2. Current-Gain — Bandwidth Product

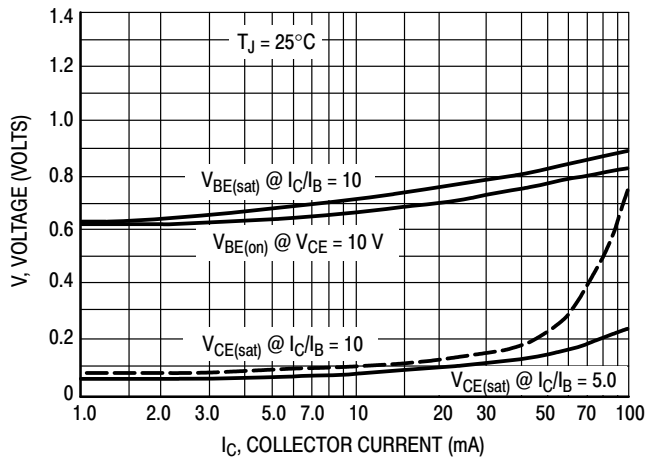


Figure 3. "On" Voltages

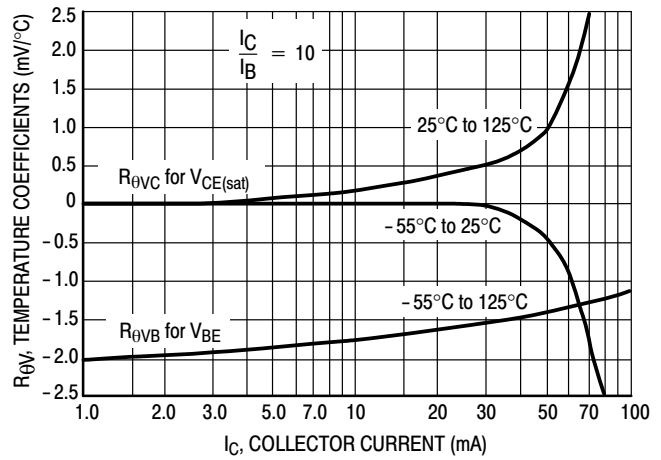


Figure 4. Temperature Coefficients

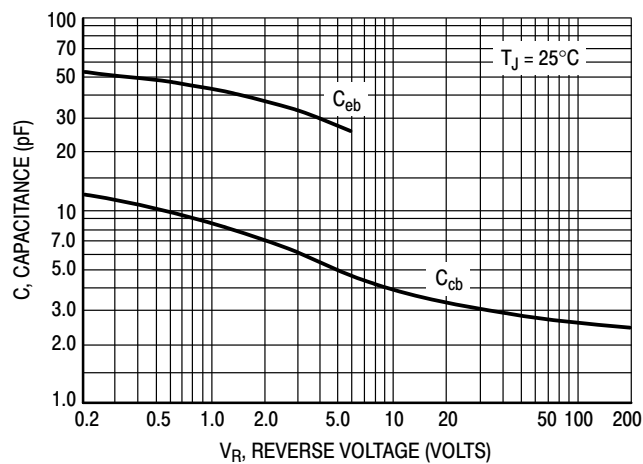


Figure 5. Capacitance

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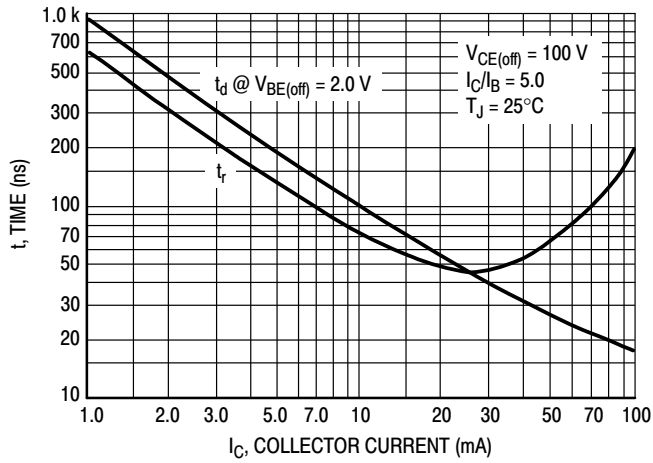


Figure 6. Turn-On Time

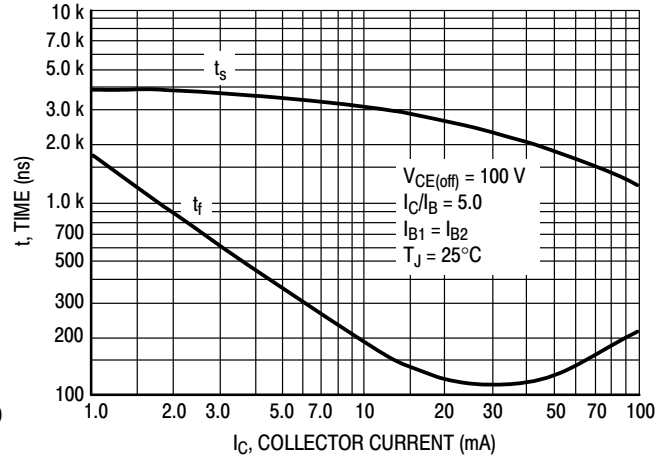


Figure 7. Turn-Off Time

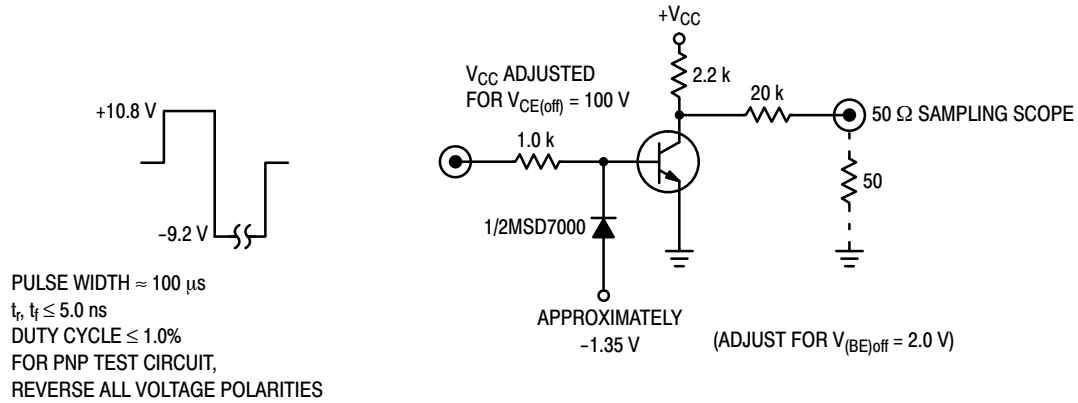


Figure 8. Switching Time Test Circuit

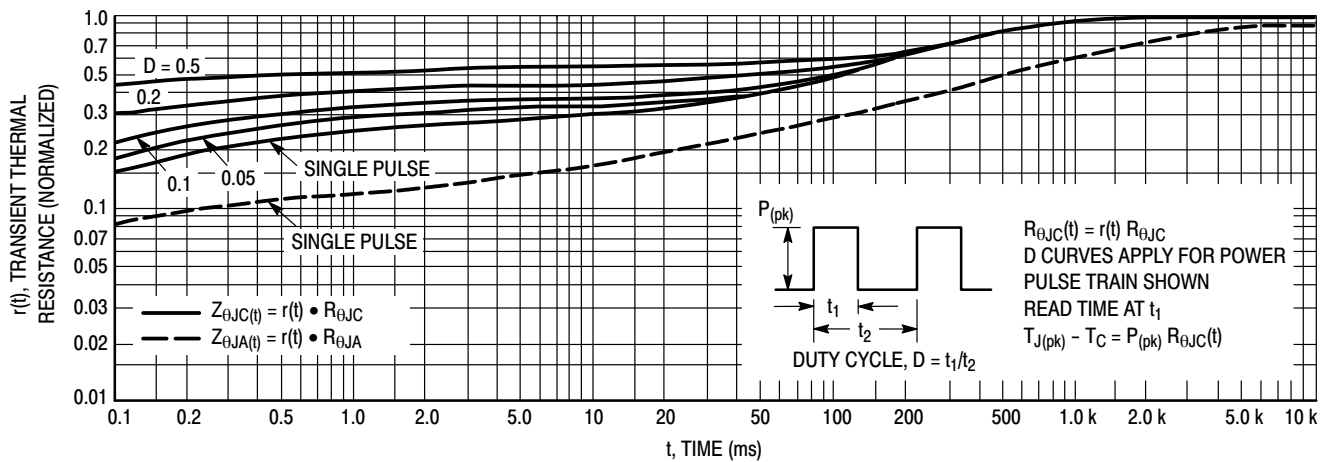
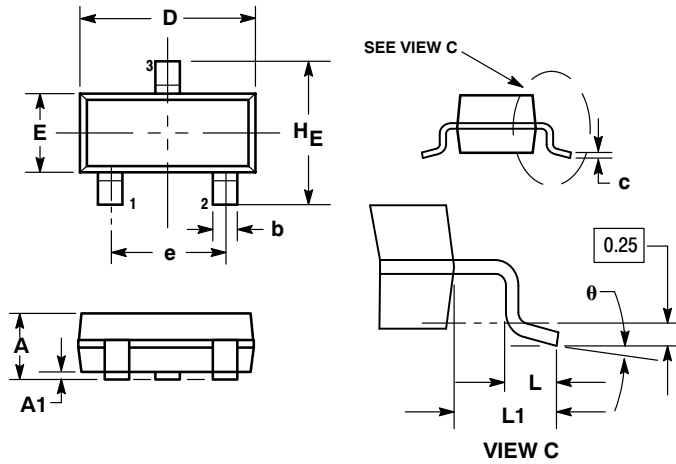


Figure 9. Thermal Response

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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN

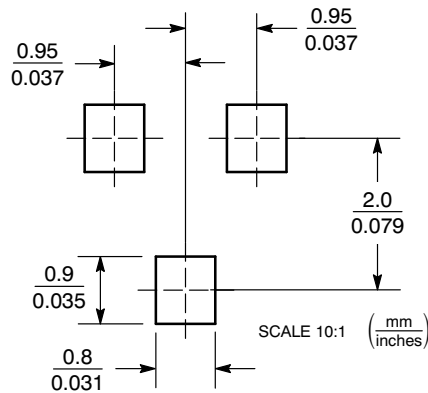


NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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